

ABSTRACT

A method for making a flash memory having a passivation layer that is not transparent to ultraviolet light. The method comprises forming a semiconductor substrate that includes a flash memory cell having a floating gate, then forming a
5 conductive layer on the substrate. Process induced charge that has accumulated on the flash cell floating gate is then neutralized and a passivation layer, which is not transparent to ultraviolet light, is formed on the conductive layer.

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